

| Ref # | Hits | Search Query   | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|------|--|---|------------------|---------|------------------|
| L1    | 727  | 349/38   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2005/07/04 16:17 |
| L2    | 27   | 1 and (gate scanning) with oxide adj layer             | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2005/07/04 16:17 |
| L3    | 672  | 349/39   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2005/07/04 16:17 |
| L4    | 10   | 1 and storage with oxide adj layer                     | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2005/07/04 16:19 |
| L5    | 19   | 1 and capacit\$4 with oxide adj layer                  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2005/07/04 16:22 |
| L6    | 149  | 1 and thin adj film with (opening contact\$3 adj hole) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2005/07/04 16:24 |
| L7    | 100  | 6 and silicon adj (oxide nitride)                      | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2005/07/04 16:24 |
| L8    | 23   | 6 and top adj gate                                     | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2005/07/04 16:28 |
| L9    | 73   | 1 and semiconductor adj energy                         | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2005/07/04 16:35 |
| L10   | 52   | 3 and semiconductor adj energy                         | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2005/07/04 16:35 |